

In the Claims:**BEST AVAILABLE COPY**

1. (Currently amended) A semiconductor light emitting device of a II-VI group compound semiconductor formed on a compound semiconductor substrate and having comprising an active layer between an n-type cladding layer and a p-type cladding layer, further comprising
- an i-type semiconductor barrier layer consisting of a single monolayer of an i-type semiconductor material having a band gap larger than a band gap of said p-type cladding layer, provided between and respectively directly in contact with said active layer and said p-type cladding layer.
2. (Withdrawn) The semiconductor light emitting device according to claim 1, wherein
- said light emitting device of the II-VI group compound is a ZnSe based light emitting device;
- said n-type cladding layer is an n-type  $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$  ( $0 < x < 1$ ,  $0 < y < 1$ ) layer; and
- said p-type cladding layer is a p-type  $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$  ( $0 < x < 1$ ,  $0 < y < 1$ ) layer.
3. (Original) The semiconductor light emitting device according to claim 1, wherein
- magnitude of the band gap of said barrier layer is larger by 0.025 eV to 0.5 eV than the band gap of said p-type cladding layer.

1 4. (Previously presented) The semiconductor light emitting  
2 device according to claim 1, wherein

3 in the band gap of said barrier layer, energy of  
4 valence band is approximately the same as or higher than  
5 that of said p-type cladding layer, and energy of  
6 conductive band is larger than that of said p-type cladding  
7 layer.

1 5. (Original) The semiconductor light emitting device  
2 according to claim 1, wherein

3 said barrier layer is of a II-VI group compound  
4 semiconductor containing Be.

1 6. (Original) The semiconductor light emitting device  
2 according to claim 5, wherein

3 said barrier layer is of  $\text{Zn}_{1-x-y}\text{Mg}_x\text{Be}_y\text{Se}$  ( $0 \leq x + y \leq 1$ ,  
4  $0 < x$ ,  $0 < y$ ).

1 7. (Withdrawn) The semiconductor light emitting device  
2 according to claim 1, wherein

3 said barrier layer is of  $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$ .

Claims 8 to 10 (Canceled).

1 11. (Original) The semiconductor light emitting device  
2 according to claim 1, wherein  
3 said p-type cladding layer is formed of  
4  $(\text{Zn}_{1-x}\text{Cd}_x\text{S})_{1-z}(\text{MgS}_{1-y}\text{Se}_y)_z$  (where x, y, z satisfy  $0 < x \leq 1$ ,  
5  $0 \leq y \leq 1$ ,  $0 \leq z < 1$ ).

1 12. (Original) The semiconductor light emitting device  
2 according to claim 1, wherein  
3 thickness of said barrier layer is at least 5 nm and  
4 at most thickness of said active layer.

1 13. (Original) The semiconductor light emitting device  
2 according to claim 1, wherein  
3 an n-type ZnSe single crystal substrate is used as  
4 said compound semiconductor substrate.

1 14. (Withdrawn) The semiconductor light emitting device  
2 according to claim 1, wherein  
3 an n-type GaAs single crystal substrate is used as  
4 said compound semiconductor substrate.

1 15. (Withdrawn) The semiconductor light emitting device  
2 according to claim 1, wherein  
3 in a stacked structure including said compound  
4 semiconductor substrate constituting said ZnSe based light  
5 emitting device, deviation between a peak of X-ray

6 diffraction of a plane orientation used as an index of  
7 distortion from said substrate and a peak of X-ray  
8 diffraction of said plane orientation from said stacked  
9 structure is at most 1000 seconds.

Claims 16 to 25 (Cancelled).

[RESPONSE CONTINUES ON NEXT PAGE]

4685/WFF:he

- 5 -